MSKSEMI 美森科













ESD

VS

TSS

MOV

GDT

PIFD

MMBT2222A-MS

Product specification





FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907A-MS)

Reference News

PACKAGE OUTLINE		MARKING
1 2	1. BASE 2. EMITTER 3.COLLECTOR	1P
SOT-23		

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
lc	Collector Current -Continuous	600	mA
Pc	Collector Dissipation	300	mW
R _{eJA}	Thermal Resistance, Junction to Ambient	417	°C/W
T _J ,Tstg	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Pa rameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	l _C = 10μA, I _E =0	75			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	Ic= 10mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	l∈=10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.01	μA
Collector cut-off current	Icex	V _{CE} =30V,V _{BE(off)} =3V			0.01	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 3V, I _C =0			0.1	μA
DC current gain	h _{FE(1)} *	V _{CE} =10V, I _C = 150mA	100		300	
	h _{FE(2)}	V _{CE} =10V, I _C = 0.1mA	40			
	h _{FE(3)} *	V _{CE} =10V, I _C = 500mA	42			
Collector-emitter saturation voltage	V _{CE(sat)} *	l _C =500 mA, I _B = 50mA l _C =150 mA, I _B =15mA			1 0.3	V
Base-emitter saturation voltage	V _{BE(sat)} *	I_C =500 mA, I_B = 50mA I_C = 150 mA, I_B =15mA			2.0 1.2	V
Transition frequency	f⊤	V _{CE} =20V, I _C = 20mA, f=100MHz	300			MHz
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V			10	ns
Rise time	tr	Ic=150mA , I _{B1} = 15mA			25	ns
Storage time	ts	Vcc=30V, Ic=150mA			225	ns
Fall time	t _f	I _{B1} =-I _{B2} =15mA			60	ns

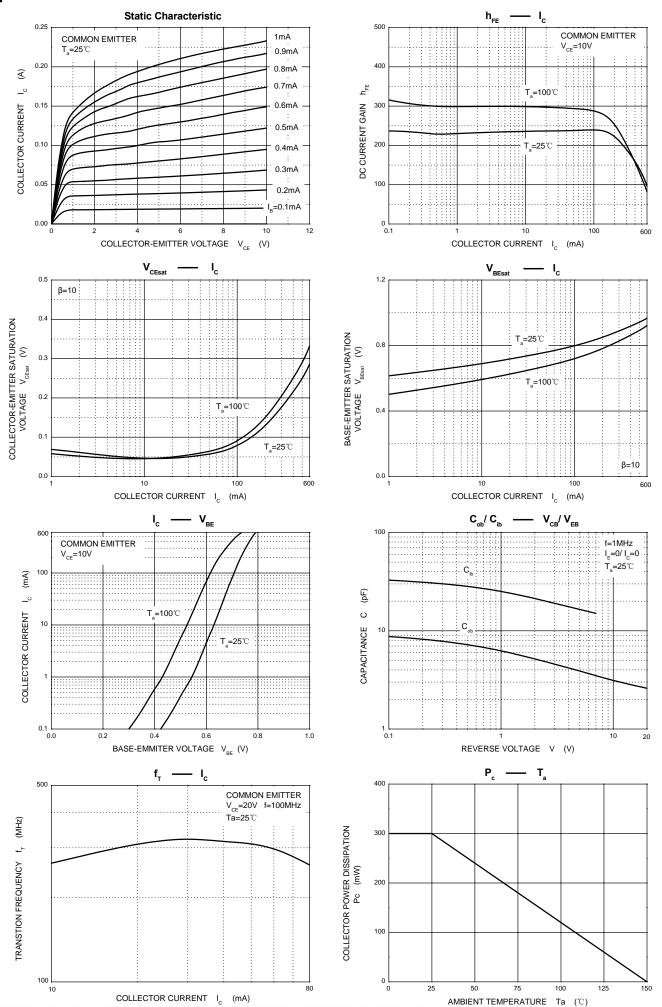
*pulse test: Pulse Width ≤300µs, Duty Cycle≤ 2.0%.

CLASSIFICATION OF h_{FE(1)}

RANK	L	Н	
RANGE 100 –200		200 –300	

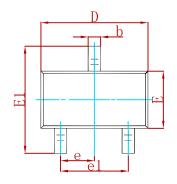


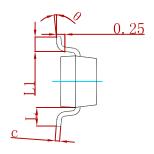
Typical Characteristics

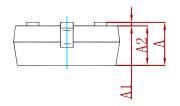




PACKAGE MECHANICAL DATA

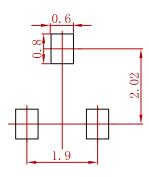






Complete	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
Ĺ	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMBT2222A-MS	SOT-23	3000



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